



CST8810B Dual N-ch 20V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

CST8810B Product Summary



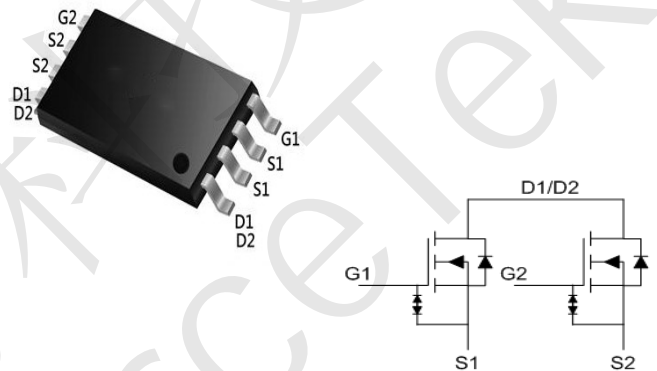
BVDSS	RDSON	ID
20V	13.5 mΩ	7A

CST8810B Description

The CST8810B is the low RDSON trenched N-CH MOSFETs with robust ESD protection. This product is suitable for Lithium-ion battery pack applications.

The CST8810B meet the RoHS and Green Product requirement with full function reliability approved.

CST8810B TSSOP8 Pin Configuration



CST8810B Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units	
V _{DSS}	Drain-Source Voltage	20	V	
V _{GSS}	Gate-Source Voltage	±10	V	
I _D	Continuous Drain Current	T _A = 25°C	7.0	A
		T _A = 100°C	4.1	A
I _{DM}	Pulsed Drain Current ^{note1}	19	A	
P _D	Power Dissipation	0.83	W	
R _{θJA}	Thermal Resistance, Junction to Ambient	151	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C	



CST8810B Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V,	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±10V	-	-	±10	uA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.4	0.7	1	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =4.5V, I _D =4A	-	13.5	18	mΩ
		V _{GS} =2.5V, I _D =3A	-	21	30	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz	-	545	-	pF
C _{oss}	Output Capacitance		-	103	-	pF
C _{rss}	Reverse Transfer Capacitance		-	90	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =4.8A, V _{GS} =4.5V	-	8	-	nC
Q _{gs}	Gate-Source Charge		-	2.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	3	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V, R _L =1.5Ω, R _{GEN} =3Ω, V _{GS} =5V	-	0.5	-	ns
t _r	Turn-on Rise Time		-	1	-	ns
t _{d(off)}	Turn-off Delay Time		-	12	-	ns
t _f	Turn-off Fall Time		-	4	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	7.0	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	19	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =4.8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



CST8810B Typical Performance Characteristics

Figure 1: Output Characteristics

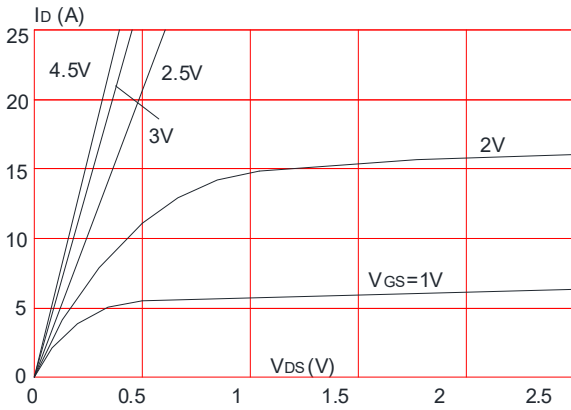


Figure 2: Typical Transfer Characteristics

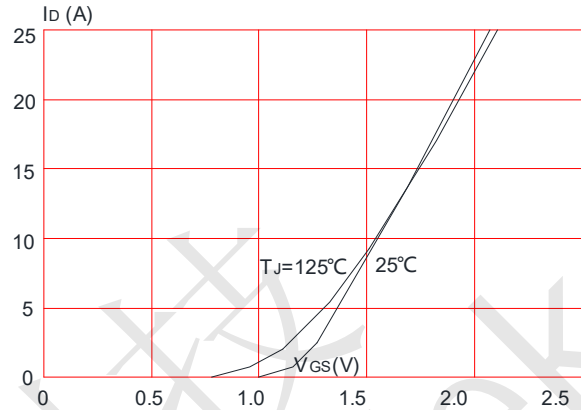


Figure 3: On-resistance vs. Drain Current

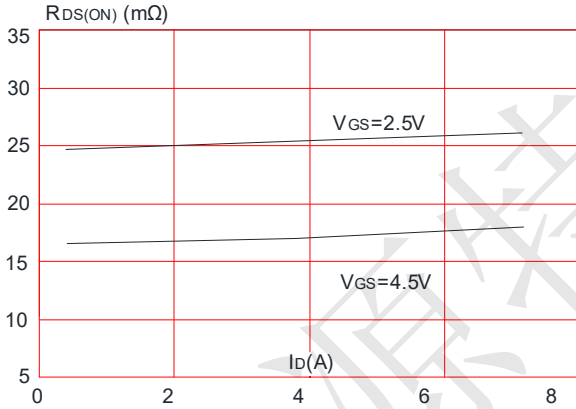


Figure 4: Body Diode Characteristics

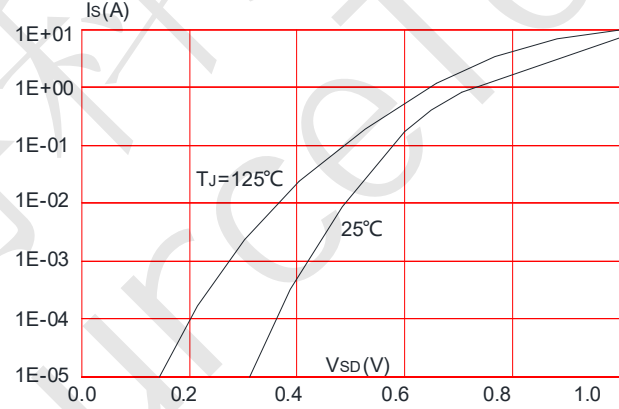


Figure 5: Gate Charge Characteristics

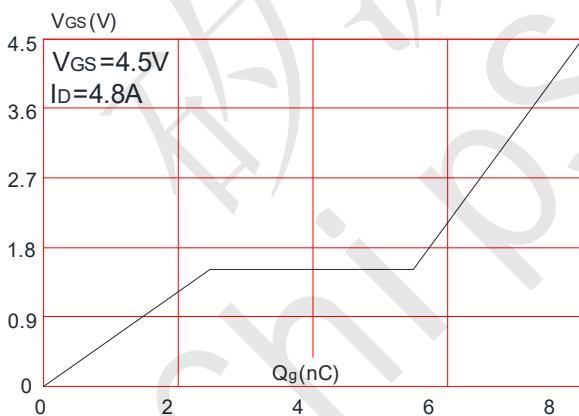
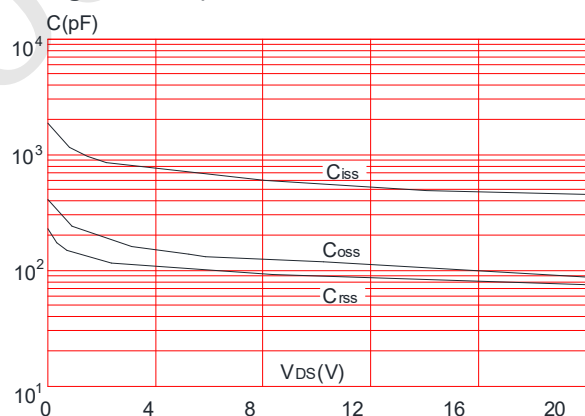


Figure 6: Capacitance Characteristics





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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

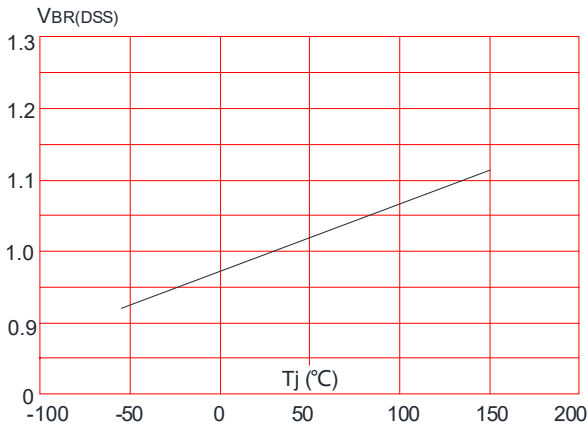


Figure 8: Normalized on Resistance vs. Junction Temperature

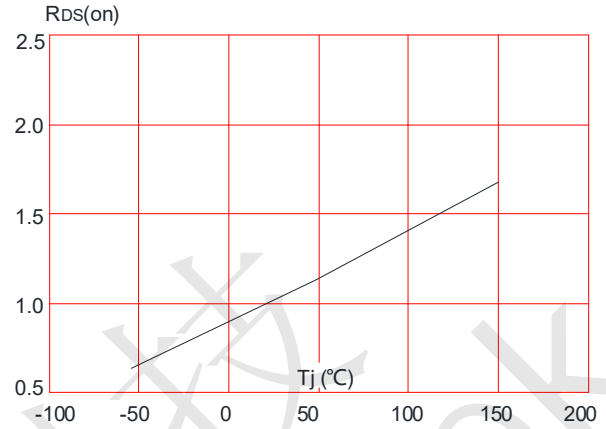


Figure 9: Maximum Safe Operating Area

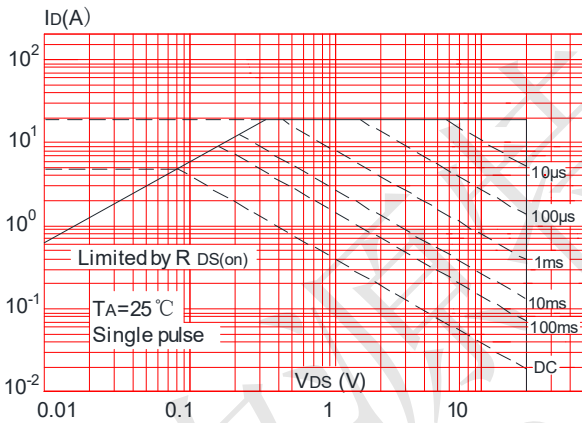


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

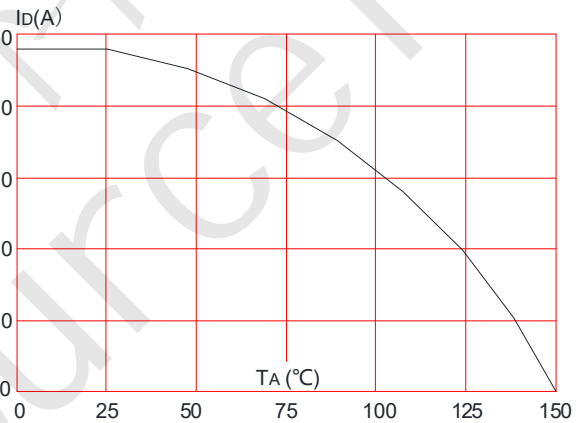
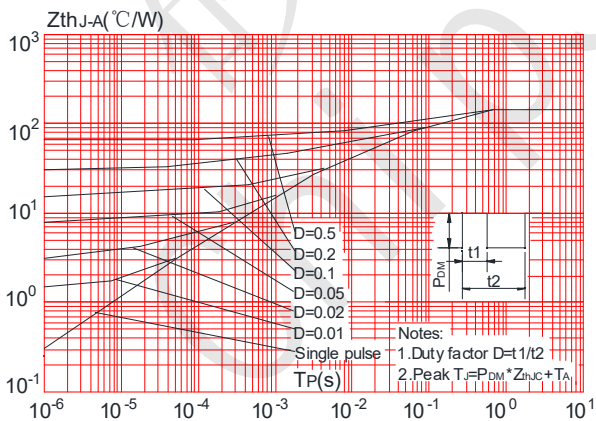


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





CST8810B Test Circuit

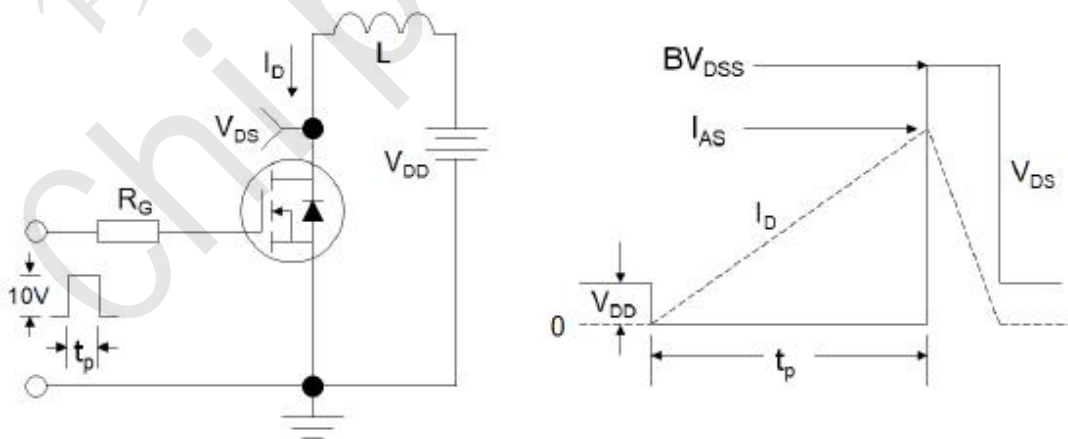
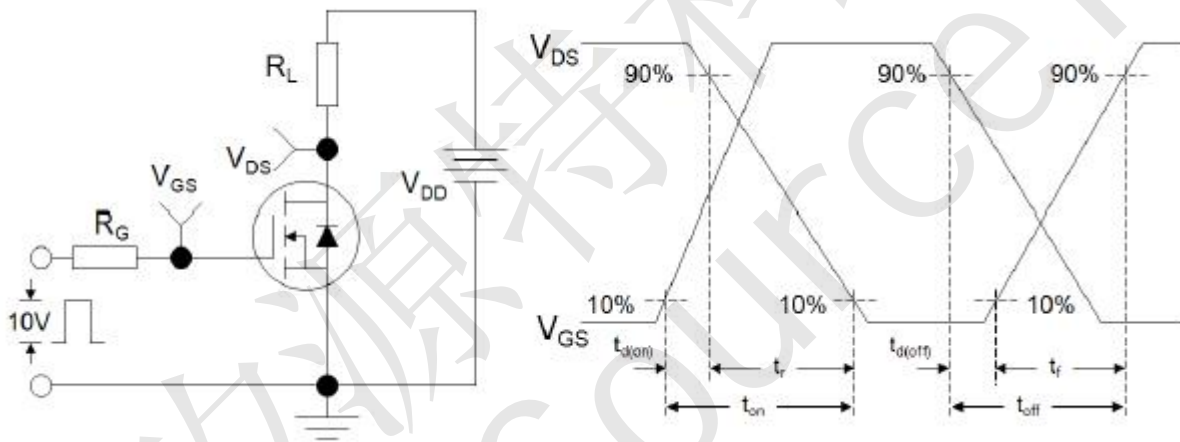
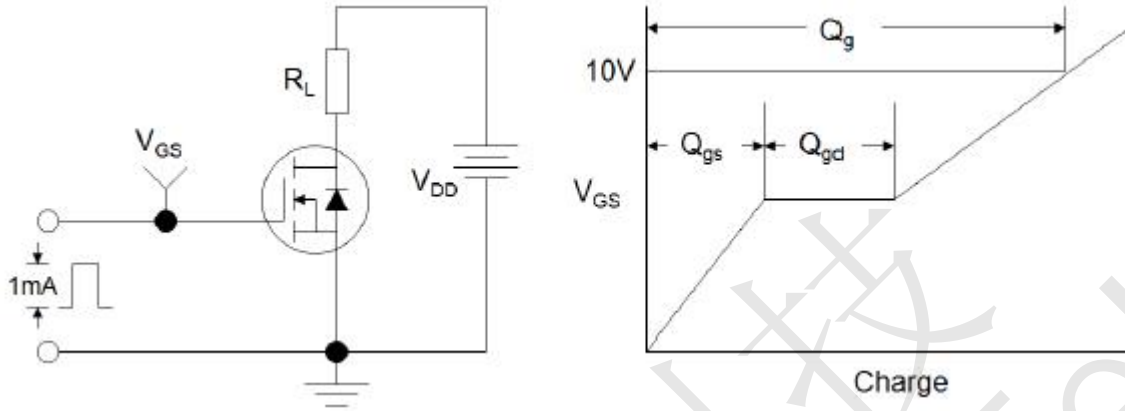
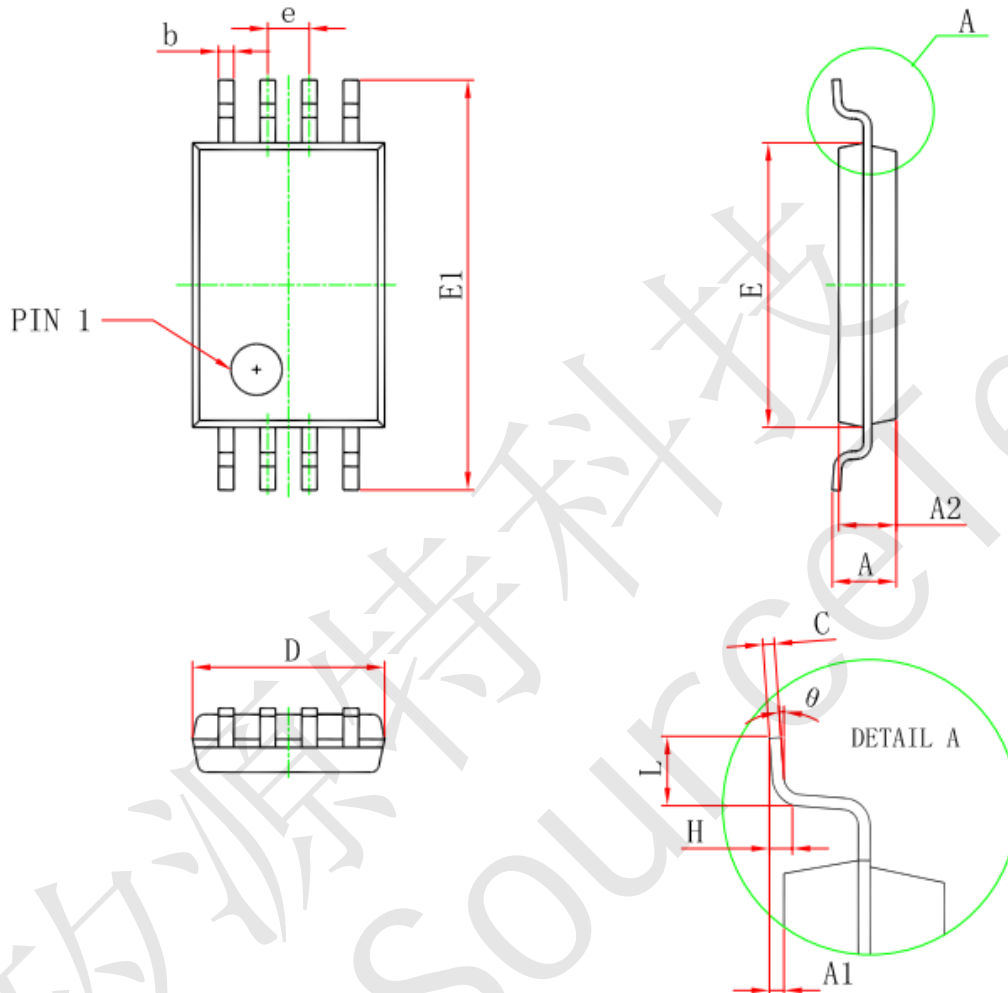


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms



CST8810B TSSOP8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
e	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.200		0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°